

APPLICATIONS: Snubber, IGBT & Power semiconductor direct mount

ELECTRICAL SPECIFICATIONS

Capacitance: 0.1 μ F
 Dissipation Factor: 0.0008 Max at 1000 Hz and 25°C
 Temperature Coefficient: 200 PPM/°C -100 PPM/°C, 100 PPM/°C
 Ripple Current: 7.5 A at 100 kHz and 30°C
 ESR: 11.5 milliohms (typical) at 100 kHz and 25°C
 Self Inductance: 1 Nanohenries maximum per mm of pitch
 dv/dt: 2050 V/ μ s

Tolerance: -10 % , +10 %
 Temperature Range: -40°C to +100°C
 Above 85°C the rated (DC/AC) voltage must be derated at per 1.5%/2.5%
 WVDG: 3000 Volts DC
 SVDC: 3500 Volts DC
 VAC: 750 Volts AC

Terminal to Terminal Dielectric strength: 1.6 times the rated DC voltage when applied between the terminals for 10 seconds
 Terminal to case Dielectric strength: 3000 VAC when applied between the terminals and case for 60 seconds

Insulation Resistance (Terminal to Terminal): 3000 MINIMUM after 100 Volts DC is applied for 60 seconds at 20°C
 Insulation resistance (Terminal to Case): Megohms MINIMUM after 0 Volts DC is applied for 0 seconds at 0

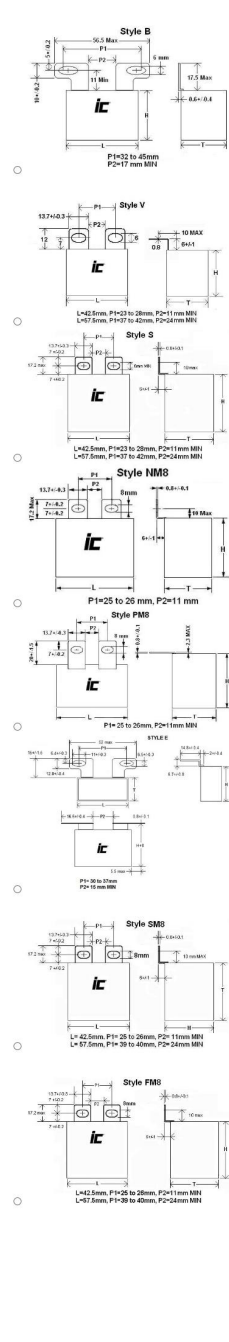
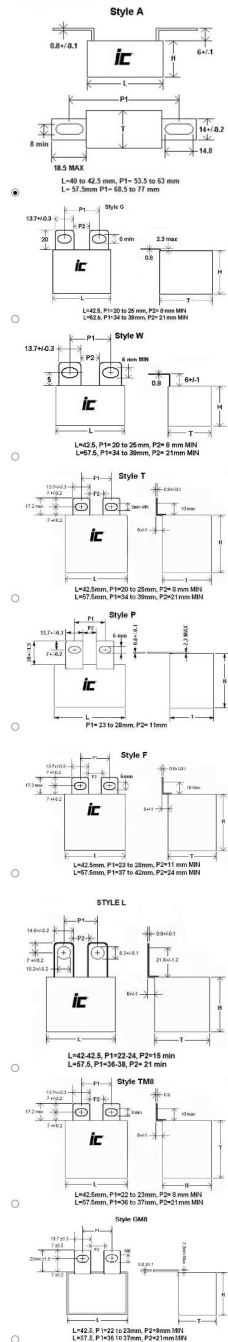
Reliability: 300 failures/billion component hours
 Load Life: 100000/30000 hours at 70°C with 100% of rated voltage
 Capacitance Change: <3% of initially measured value
 D.F. Change: <20% of maximum specified value
 I.R. Change: >50% of minimum specified value

PHYSICAL DIMENSIONS

Length (L): 42.5 mm, 0.8 mm
 Height (H): 28 mm, +/- 0.6 mm
 Thickness (T): 17 mm, +/- 0.45 mm

Lead Diameter (d): mm, +/- mm
 Lead Length (LL): mm, +/- mm

CHOOSE LEAD STYLE



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